

Amendments to the Claims

The listing of claims below will replace all prior versions and listings of claims in the application.

1. (Canceled)

2. (Currently Amended) A method for producing producing, on a substrate, an electronic component with closely adjacent electrodes on a substrate, electrodes, the method comprising:

- a) depositing a first metal layer onto the substrate;
- b) structuring a first photo lacquer on a surface of the first metal layer, wherein a portion of the surface of the first metal layer does not have the first photo lacquer thereon;
- c) etching the portion of the surface of the first metal layer not having the first photo lacquer;
- d) undercut etching the first metal layer so that an overhang is formed defined by the first photo lacquer;
- e) exposing exposing, to a metal vapor, a surface of the first photo lacquer and the an exposed portion of the surface of substrate where the first metal layer to a first metal vapor was etched away so that a second metal layer is formed on the surface of the first photo lacquer and the exposed portion of the surface of substrate where the first metal layer was etched away except in a space between the overhang and the substrate; and
- f) removing both the first photo lacquer and the second metal layer formed on from the surface of the first photo lacquer.

3. (Canceled)

4. (Currently Amended) The method of claim 2, further comprising:

- g) etching a hole into the substrate at a position other than a position of the first metal layer and the second metal layer;
- h) depositing a third metal layer onto the substrate, the first metal layer, and the second metal layer;
- i) applying an insulator onto the third metal layer;
- j) etching a portion of the insulator at the position of the first metal layer and the second metal layer;
- k) applying an organic ~~semi-conductor~~ semiconductor onto the third metal layer and the insulator; and
- l) applying a sealing layer onto the organic ~~semi-conductor~~ semiconductor and semiconductor.
- ~~m) exposing the third metal gate at a position of the hole using a photolithographic process.~~

5.-12. (Canceled)

13. (Previously Presented) The method of claim 4, wherein further comprising making the third metal layer ~~is made of~~ from gold.

14.-18. (Canceled)

19. (Currently Amended) An electronic component with closely adjacent electrodes, comprising:

a substrate;

a first electrode ~~formed~~ on the substrate;

a second electrode ~~formed~~ on the ~~substrate in which~~ substrate, wherein a separation between the first electrode and the second electrode is between ten nanometers and ~~two thousand~~ one hundred nanometers;

a third electrode ~~formed~~ in a hole in the ~~substrate in~~ substrate, wherein the third electrode is positioned within the separation between the first electrode and the second electrode;

an insulator ~~formed~~ on the third electrode;

an organic ~~semi-conductor~~ semiconductor on the first electrode, the second electrode, and the insulator; and

a sealing layer ~~formed~~ on the organic ~~semi-conductor~~; semiconductor.

~~wherein the separation between the first electrode and the second electrode is formed by forming a photo lacquer layer on a portion of a first metal layer formed on the substrate, etching a portion of the first metal layer, undercut etching the first metal layer to produce an overhang of the photo lacquer layer, depositing a second metal layer on the substrate at a position of the portion of the first metal layer, and removing the photo lacquer layer.~~

20. (Currently Amended) The electronic component of claim 19, wherein the substrate is ~~made of at least one of~~ comprises either a polymer film and or a glass. glass other than SiO₂.

21. (Currently Amended) The electronic component of claim 19, wherein the first electrode is made of at least one of comprises either chromium and or gold.

22. (Previously Presented) The electronic component of claim 19, wherein the third electrode is made of comprises gold.

23. (New) A device, comprising:

a first electrode on a substrate comprising a glass other than SiO₂;

a second electrode on the substrate and separated between ten nanometers and one hundred nanometers from the first electrode;

a third electrode in a hole in the substrate, wherein the third electrode is positioned between the first electrode and the second electrode;

an insulator on the third electrode;

a semiconductor on the first electrode, the second electrode, and the insulator; and

a sealing layer on the semiconductor.

24. (New) The electronic component of claim 23, wherein the first electrode comprises either chromium or gold.

25. (New) The electronic component of claim 23, wherein the third electrode comprises gold.